

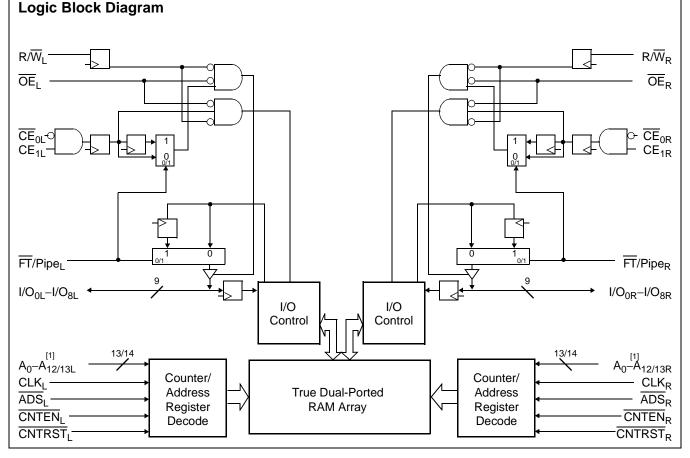
CY7C09159AV CY7C09169AV

3.3V 8K/16K x 9 Synchronous Dual Port Static RAM

Features

- True Dual-Ported memory cells which allow simultaneous access of the same memory location
- Two Flow-Through/Pipelined devices
 - -8K x 9 organization (CY7C09159AV)
 - -16K x 9 organization (CY7C09169AV)
- Three Modes
 - Flow-Through
 - Pipelined
 - -Burst
- Pipelined output mode on both ports allows fast 83-MHz operation
- 0.35-micron CMOS for optimum speed/power

- High-speed clock to data access 9 and 12 ns (max.)
- 3.3V Low operating power
 - Active = 135 mA (typical)
 - Standby = 10 μ A (typical)
- Fully synchronous interface for easier operation
- Burst counters increment addresses internally
 - -Shorten cycle times
 - Minimize bus noise
 - -Supported in Flow-Through and Pipelined modes
- Dual Chip Enables for easy depth expansion
- Automatic power-down
- · Commercial and industrial temperature ranges
- Available in 100-pin TQFP



Notes:

1. $A_0 - A_{12}$ for 8K; $A_0 - A_{13}$ for 16K.

For the most recent information, visit the Cypress web site at www.cypress.comCypress Semiconductor Corporation• 3901 North First Street• San Jose• CA 95134• 408-943-2600Document #: 38-06053 Rev. *ARevised December 27, 2002



Functional Description

The CY7C09159AV and CY7C09169AV are high-speed synchronous CMOS 8K and 16K x 9 dual-port static RAMs. Two ports are provided, permitting independent, simultaneous access for reads and writes to any location in memory.^[2] Registers on control, address, and data lines allow for minimal setup and hold times. In pipelined output mode, data is registered for decreased cycle time. Clock to data valid $t_{CD2} = 9$ ns (pipelined). Flow-through mode can also be used to bypass the pipelined output register to eliminate access latency. In flow-through mode data will be available $t_{CD1} = 18$ ns after the address is clocked into the device. Pipelined output or flow-through mode is selected via the FT/Pipe pin.

Each port contains a burst counter on the input address register. The internal write pulse width is independent of the LOWto-HIGH transition of the clock signal. The internal write pulse is self-timed to allow the shortest possible cycle times. A HIGH on \overline{CE}_0 or LOW on CE_1 for one clock cycle will power down the internal circuitry to reduce the static power consumption. The use of multiple Chip Enables allows easier banking of multiple chips for depth expansion configurations. In the pipelined mode, one cycle is required with \overline{CE}_0 LOW and CE_1 HIGH to reactivate the outputs.

Counter enable inputs are provided to stall the operation of the address input and utilize the internal address generated by the internal counter for fast interleaved memory applications. A port's burst counter is loaded with the port's Address Strobe (ADS). When the port's Count Enable (CNTEN) is asserted, the address counter will increment on each LOW-to-HIGH transition of that port's clock signal. This will read/write one word from/into each successive address location until CNTEN is deasserted. The counter can address the entire memory array and will loop back to the start. Counter Reset (CNTRST) is used to reset the burst counter.

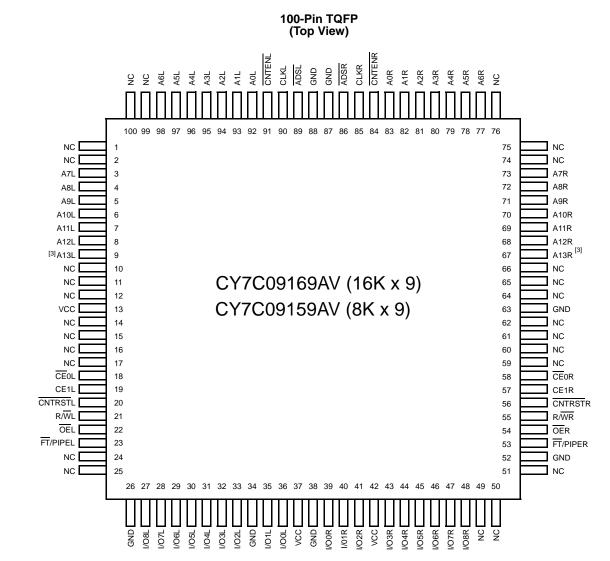
All parts are available in 100-pin Thin Quad Plastic Flatpack (TQFP) packages.

Note:

2. When simultaneously writing to the same location, final value cannot be guaranteed.



Pin Configuration



Note:

3. This pin is NC for CY7C09159AV.

Selection Guide

	CY7C09159AV CY7C09169AV -9	CY7C09159AV CY7C09169AV -12
f _{MAX2} (MHz) (Pipelined)	67	50
Max Access Time (ns) (Clock to Data, Pipelined)	9	12
Typical Operating Current I _{CC} (mA)	135	115
Typical Standby Current for I _{SB1} (mA) (Both Ports TTL Level)	20	20
Typical Standby Current for I_{SB3} (µA) (Both Ports CMOS Level)	10 µA	10 µA



Pin Definitions

Left Port	Right Port	Description				
A _{0L} -A _{13L}	A _{0R} -A _{13R}	Address Inputs (A ₀ -A ₁₂ for 8K; A ₀ -A ₁₃ for 16K devices).				
ADSL	ADS _R	Address Strobe Input. Used as an address qualifier. This signal should be asserted LOW during normal read or write transactions. Asserting this signal LOW also loads the burst address counter with data present on the I/O pins.				
CE _{0L} ,CE _{1L}	CE _{0R} ,CE _{1R}	Chip Enable Input. To select either the left or right port, both \overline{CE}_0 AND CE_1 must be asserted to their active states ($\overline{CE}_0 \le V_{IL}$ and $CE_1 \ge V_{IH}$).				
CLKL	CLK _R	Clock Signal. This input can be free-running or strobed. Maximum clock input rate is f _{MAX.}				
CNTENL	CNTENR	Counter Enable Input. Asserting this signal <u>LOW increments the burst address counter of its</u> respective port on each rising edge of CLK. CNTEN is disabled if ADS or CNTRST are asserted LOW.				
CNTRST	CNTRST _R	Counter Reset Input. Asserting this signal LOW resets the burst address counter of its respective port to zero. CNTRST is not disabled by asserting ADS or CNTEN.				
I/O _{0L} -I/O _{8L}	I/O _{0R} -I/O _{8R}	Data Bus Input/Output (I/O ₀ –I/O ₇ for x8 devices; I/O ₀ –I/O ₈ for x9 devices).				
OEL	OE _R	Output Enable Input. This signal must be asserted LOW to enable the I/O data pins during read operations.				
R/WL	R/W _R	Read/Write Enable Input. This signal is asserted LOW to write to the dual-port memory array. For read operations, assert this pin HIGH.				
FT/PIPE _L	FT/PIPE _R	Flow-Through/Pipelined Select Input. For flow-through mode operation, assert this pin LOW. For pipelined mode operation, assert this pin HIGH.				
GND		Ground Input.				
NC		No Connect.				
V _{CC}		Power Input.				

Maximum Ratings [4]

(Above which the useful life may be impaired. For user guide-lines, not tested.)
Storage Temperature65°C to +150°C
Ambient Temperature with Power Applied55°C to +125°C
Supply Voltage to Ground Potential0.5V to +4.6V
DC Voltage Applied to Outputs in High Z State0.5V to V _{CC} +0.5V
DC Input Voltage0.5V to $V_{CC}\text{+}0.5\text{V}$

Operating Range

Range	Ambient Temperature	v _{cc}
Commercial	0°C to +70°C	$3.3V\pm300~mV$
Industrial ^[5]	–40°C to +85°C	$3.3V\pm300~mV$

Output Current into Outputs (LOW)...... 20 mA Static Discharge Voltage>2001V Latch-Up Current......>200 mA

Note:

The voltage on any input or I/O pin can not exceed the power pin during power-up
 Industrial parts are available in CY7C09169AV only.



Electrical Characteristics Over the Operating Range

				CY7C09159AV CY7C09169AV					
				-9			-12		
Parameter	Description		Min.	Тур.	Max.	Min.	Тур.	Max.	Unit
V _{OH}	Output HIGH Voltage (V _{CC} = Min., I _{OH} = -4.0 m	nA)	2.4			2.4			V
V _{OL}	Output LOW Voltage (V _{CC} = Min., I _{OH} = +4.0 m	A)			0.4			0.4	V
V _{IH}	Input HIGH Voltage		2.0			2.0			V
V _{IL}	Input LOW Voltage				0.8			0.8	V
I _{OZ}	Output Leakage Current	Output Leakage Current				-10		10	μΑ
I _{CC}	Operating Current (V _{CC} = Max.,	Com'l.		135	230		115	180	mA
	I _{OUT} = 0 mA) Outputs Disabled	Ind. ^[5]					155	250	mA
I _{SB1}	Standby Current (Both Ports TTL Level) ^[6]	Com'l.		20	75		20	70	mA
	$CE_L \& CE_R \ge V_{IH}, f = f_{MAX}$	Ind. ^[5]					30	80	mA
I _{SB2}	Standby_Current (One Port TTL Level) ^[6]	Com'l.		95	155		85	140	mA
	$\overline{CE}_{L} \mid \overline{CE}_{R} \ge V_{IH}, f = f_{MAX}$	Ind. ^[5]					95	150	mA
I _{SB3}	Standby Current (Both Ports CMOS Level) ^[6]	Com'l.		10	500		10	500	μΑ
	$\overline{CE}_{L} \& \overline{CE}_{R} \ge V_{CC} - 0.2V, f = 0$		1		•		10	500	μΑ
I _{SB4}	Standby Current (One Port CMOS Level) ^[6]	Com'l.	1	85	115		75	100	mA
	$CE_L \mid CE_R \ge V_{IH}, f = f_{MAX}$	Ind. ^[5]	1				85	110	mA

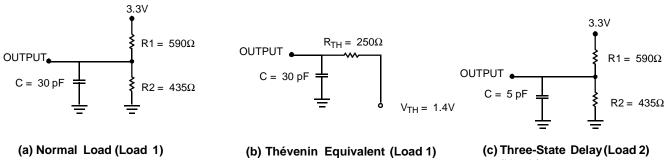
Capacitance

Parameter	Description	Test Conditions	Max.	Unit
C _{IN}	Input Capacitance	$T_A = 25^{\circ}C, f = 1 \text{ MHz},$	10	pF
C _{OUT}	Output Capacitance	$V_{CC} = 3.3V$	10	pF

Note: 6. \overline{CE}_L and \overline{CE}_R are internal signals. To select either the left or right port, both \overline{CE}_0 AND CE_1 must be asserted to their active states ($\overline{CE}_0 \le V_{IL}$ and $CE_1 \ge V_{IH}$).



AC Test Loads



(Used for t_{CKLZ} , t_{OLZ} , & t_{OHZ} including scope and jig)



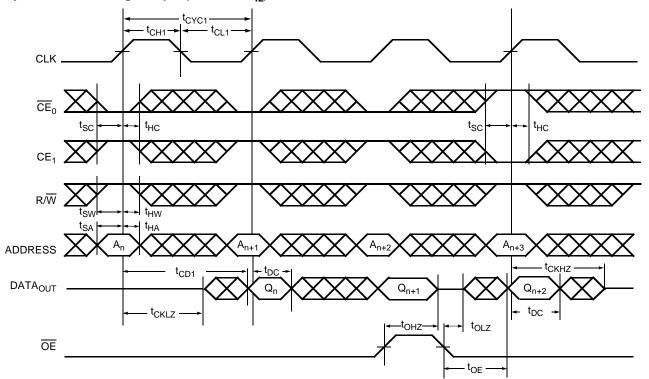
Switching Characteristics Over the Operating Range

		CY7C09159AV					
			-9	-			
Parameter	Description	Min.	Max.	Min.	Max.	Unit	
f _{MAX1}	f _{Max} Flow-Through		40		33	MHz	
f _{MAX2}	f _{Max} Pipelined		67		50	MHz	
t _{CYC1}	Clock Cycle Time - Flow-Through	25		30		ns	
t _{CYC2}	Clock Cycle Time - Pipelined	15		20		ns	
t _{CH1}	Clock HIGH Time - Flow-Through	12		12		ns	
t _{CL1}	Clock LOW Time - Flow-Through	12		12		ns	
t _{CH2}	Clock HIGH Time - Pipelined	6		8		ns	
t _{CL2}	Clock LOW Time - Pipelined	6		8		ns	
t _R	Clock Rise Time		3		3	ns	
t _F	Clock Fall Time		3		3	ns	
t _{SA}	Address Set-up Time	4		4	1	ns	
t _{HA}	Address Hold Time	1		1		ns	
t _{SC}	Chip Enable Set-up Time	4		4		ns	
t _{HC}	Chip Enable Hold Time	1		1		ns	
t _{SW}	R/W Setup Time	4		4		ns	
t _{HW}	R/W Hold Time	1		1		ns	
t _{SD}	Input Data Set-up Time	4		4		ns	
t _{HD}	Input Data Hold Time	1		1		ns	
t _{SAD}	ADS Set-up Time	4		4		ns	
t _{HAD}	ADS Hold Time	1		1		ns	
t _{SCN}	CNTEN Set-up Time	4		4		ns	
t _{HCN}	CNTEN Hold Time	1		1		ns	
t _{SRST}	CNTRST Set-up Time	4		4		ns	
t _{HRST}	CNTRST Hold Time	1		1		ns	
t _{OE}	Output Enable to Data Valid		10		12	ns	
t _{OLZ}	OE to Low Z	2		2		ns	
t _{OHZ}	OE to High Z	1	7	1	7	ns	
t _{CD1}	Clock to Data Valid - Flow-Through		20		25	ns	
t _{CD2}	Clock to Data Valid - Pipelined		9		12	ns	
t _{DC}	Data Output Hold After Clock HIGH	2		2		ns	
t _{СКНZ}	Clock HIGH to Output High Z	2	9	2	9	ns	
t _{CKLZ}	Clock HIGH to Output Low Z	2		2		ns	
Port to Port D	Delays						
t _{CWDD}	Write Port Clock High to Read Data Delay		40		40	ns	
t _{CCS}	Clock to Clock Set-up Time		15		15	ns	

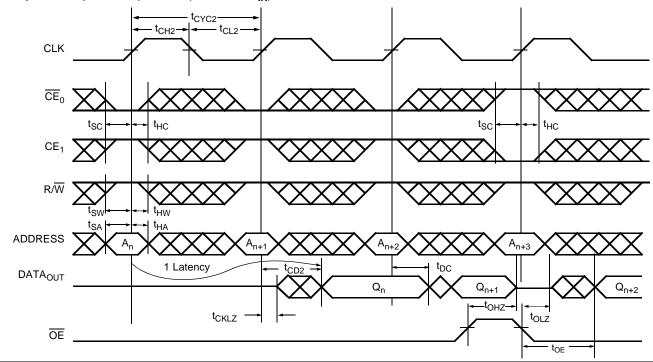


Switching Waveforms

Read Cycle for Flow-Through Output ($\overline{FT}/PIPE = V_{II}$)^[7, 8, 9, 10]



Read Cycle for Pipelined Operation ($\overline{FT}/PIPE = V_{IH}$)^[7, 8, 9, 10]

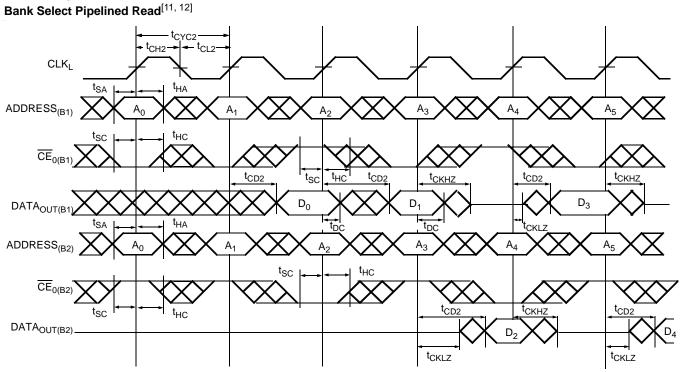


Notes:

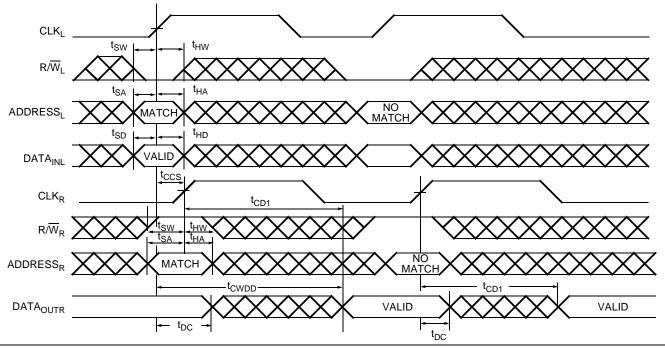
- 7. 8.
- 9.
- \overline{OE} is asynchronously controlled; all other inputs are synchronous to the rising clock edge. ADS = V_{IL}, CNTEN and CNTRST = V_{IH} The output is disabled (high-impedance state) by $\overline{CE}_0 = V_{IL}$ or $CE_1 = V_{IL}$ following the next rising edge of the clock. Addresses do not have to be accessed sequentially since ADS = V_{IL} constantly loads the address on the rising edge of the CLK. Numbers are for reference only. 10.

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Left Port Write to Flow-Through Right Port Read^[13, 14, 15, 16]

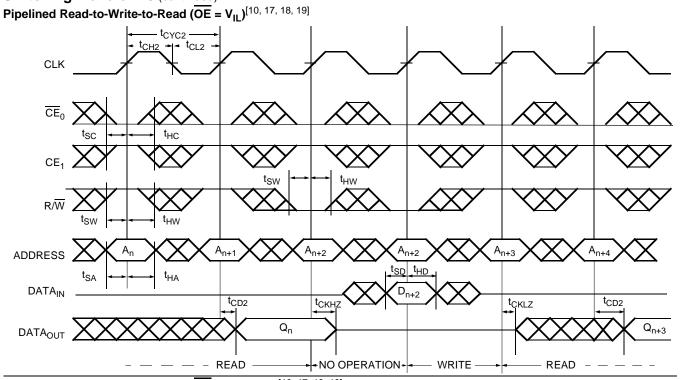


Notes:

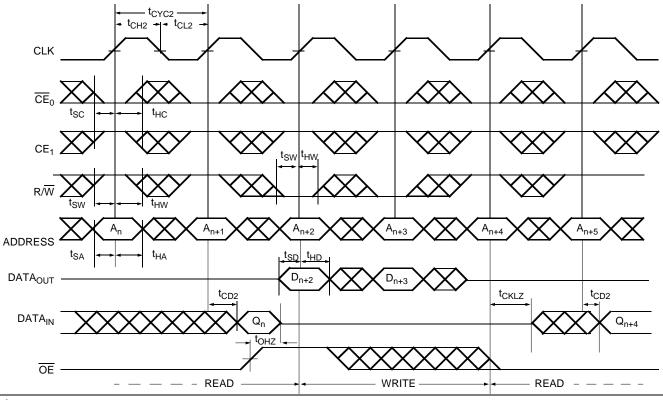
- 11. In this depth expansion example, B1 represents Bank #1 and B2 is Bank #2; Each Bank consists of one Cypress dual-port device from this data sheet. <u>ADDRESS_(B1) = ADDRESS_(B2).
 12. OE and ADS = V_{IL}; CE_{1(B1)}, CE_{1(B2)}, R/W, CNTEN, and CNTRST = V_{IH}.
 13. <u>The same waveforms apply for a right port write to</u> flow-through left port read.
 14. <u>CE₀ and ADS = V_{IL}; CE₁, CNTEN, and CNTRST = V_{IH}.
 15. OE = V_{IL} for the right port, which is being read from. OE = V_{IH} for the left port, which is being written to.
 </u></u>

- It t_{CCS} ≤ maximum specified, then data from right port READ is not valid until the maximum specified for t_{CWDD}. If t_{CCS}>maximum specified, then data is not 16. valid until t_{CCS} + t_{CD1}. t_{CWDD} does not apply in this case.





Pipelined Read-to-Write-to-Read (OE Controlled)^[10, 17, 18, 19]

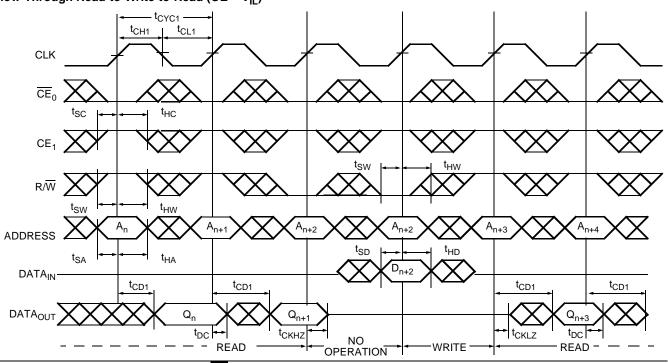


Notes:

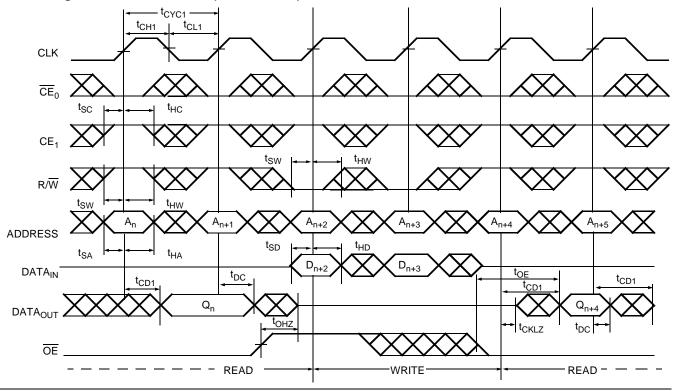
17. Output state (HIGH, LOW, or High-Impedance) is determined by the previous cycle control signals.
 18. CE₀ and ADS = V_{IL}; CE₁, CNTEN, and CNTRST = V_{IH}.
 19. During "No operation," data in memory at the selected address may be corrupted and should be rewritten to ensure data integrity.



Flow-Through Read-to-Write-to-Read ($\overline{OE} = V_{IL}$)^[8, 10, 17, 18, 19]

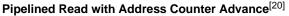


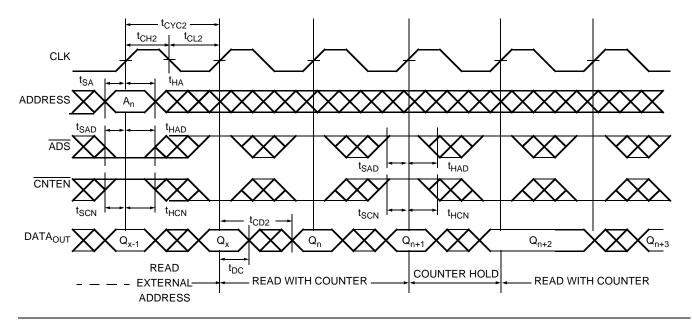
Flow-Through Read-to-Write-to-Read (OE Controlled)^[8, 10, 17, 18, 19]



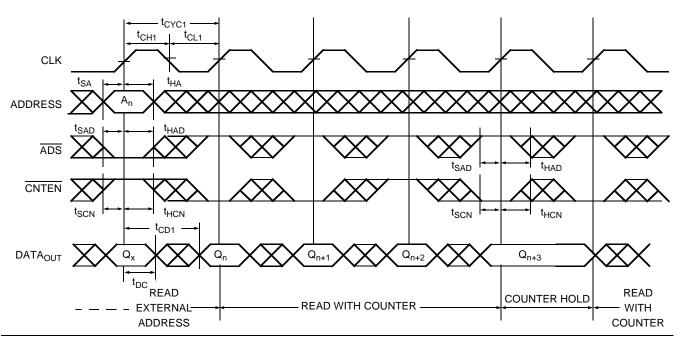
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Flow-Through Read with Address Counter Advance^[20]

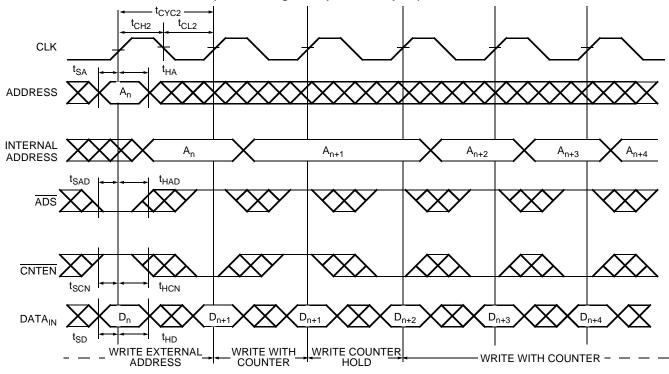


Note:

20. \overline{CE}_0 and $\overline{OE} = V_{IL}$; CE_1 , R/W and $\overline{CNTRST} = V_{IH}$.



Write with Address Counter Advance (Flow-Through or Pipelined Outputs)^[21, 22]

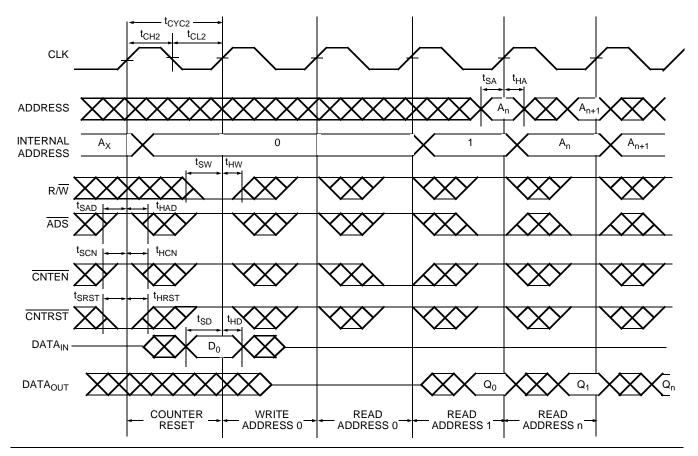


Notes:

21. \overline{CE}_0 and $R/\overline{W} = V_{IL}$; CE_1 and $\overline{CNTRST} = V_{IH}$. 22. The "Internal Address" is equal to the "External Address" when $\overline{ADS} = V_{IL}$ and equals the counter output when $\overline{ADS} = V_{IH}$.



Counter Reset (Pipelined Outputs)^[10, 17, 23, 24]



Notes:

23. $\overline{CE}_0 = V_{IL}$; $CE_1 = V_{IH}$. 24. No dead cycle exists during counter reset. A READ or WRITE cycle may be coincidental with the counter reset.



Read/Write and Enable Operation^[25, 26, 27]

		Inputs				
OE	CLK	CE0	CE1	R/W	I/O ₀ –I/O ₉	Operation
Х		Н	Х	Х	High-Z	Deselected ^[28]
Х		Х	L	Х	High-Z	Deselected ^[28]
Х	L.	L	Н	L	D _{IN}	Write
L	Г	L	Н	Н	D _{OUT}	Read ^[28]
Н	Х	L	Н	Х	High-Z	Outputs Disabled

Address Counter Control Operation^[25, 29, 30, 31]

Address	Previous Address	CLK	ADS	CNTEN	CNTRST	I/O	Mode	Operation
Х	Х	μ	Х	Х	L	D _{out(0)}	Reset	Counter Reset to Address 0
A _n	Х	μ	L	Х	Н	D _{out(n)}	Load	Address Load into Counter
Х	A _n	μ	Н	Н	Н	D _{out(n)}	Hold	External Address Blocked—Counter Disabled
Х	A _n	μ	Н	L	Н	D _{out(n+1)}	Increment	Counter Enabled—Internal Address Generation

Notes:

 Notes:

 25. "X" = "don't care," "H" = V_{IH}, "L" = V_{IL}.

 6. ADS, CNTEN, CNTRST = "don't care."

 27. OE is an asynchronous input signal.

 28. When CE_changes state in the pipelined mode, deselection and read happen in the following clock cycle.

 29. CE₀ and OE = V_{IL}; CE₁ and RW = V_{IH}.

 30. Data shown for Flow-through mode; pipelined mode output will be delayed by one cycle.

 31. Counter operation is independent of CE₀ and CE₁.



Ordering Information

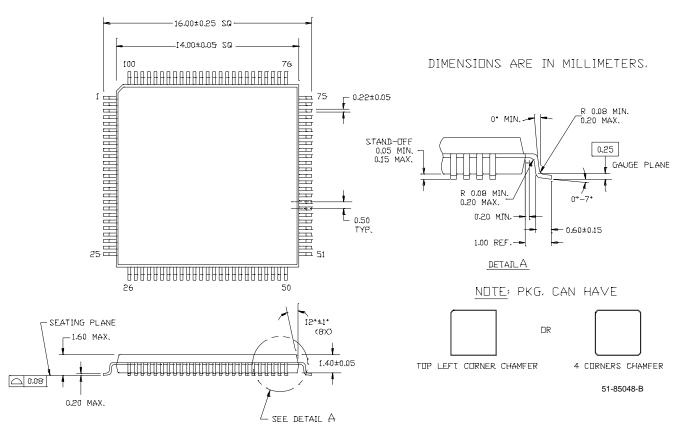
8K x9 3.3V Synchronous Dual-Port SRAM

Speed (ns)	Ordering Code Package Name		Package Type	Operating Range
9	CY7C09159AV-9AC	A100	100-Pin Thin Quad Flat Pack	Commercial
12	CY7C09159AV-12AC	A100	100-Pin Thin Quad Flat Pack	Commercial

16K x9 3.3V Synchronous Dual-Port SRAM

Speed (ns)	Ordering Code	Package Ordering Code Name Package Type		Operating Range
9	CY7C09169AV-9AC	A100	100-Pin Thin Quad Flat Pack	Commercial
12	CY7C09169AV-12AC	A100	100-Pin Thin Quad Flat Pack	Commercial
	CY7C09169AV-12AI	A100	100-Pin Thin Quad Flat Pack	Industrial

Package Diagram

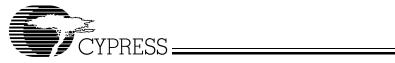


100-Pin Thin Plastic Quad Flat Pack (TQFP) A100

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REV.	ECN NO.	Issue Orig. of CN NO. Date Change		Description of Change			
**	110205	11/15/01	SZV	Change from Spec number: 38-00839 to 38-06053			
*A	122303	12/27/02	RBI	Power up requirements added to Maximum Ratings Information			

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